

FORM PTO-1449  
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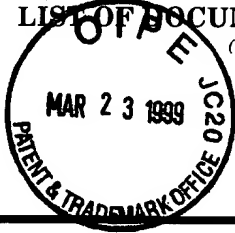
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09/216,214

## LIST OF DOCUMENTS CITED BY APPLICANT

(Use several sheets if necessary)



APPLICANT

Robert Havemann

FILING DATE

12/18/98

GROUP

2812

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
TT	AA	5,439,846	8/8/95	Nguyen, et al.	437/187		12/17/93
TT	AB	5,196,360	3/23/93	Doan, et al.	437/41		4/6/92
TT	AC	5,395,785	3/7/95	Nguyen, et al.	437/52		12/17/93
	AD						
	AE						
	AF						
	AG						

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## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AH							
	AI							

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TT	AK	1992 IEEE "Reverse Elevated Source/Drain (RES) MOSFET for Deep Submicron CMOS," pp. IEDM 92-885 thru IEDM 92-888 (J.R. Pfister, M. Woo, J.T. Fitch and J. Schmidt)						
TT	AL	Silicon Processing for the VLSI ERA - Volume II, Chapter 3, beginning with "Contact Technology and Local Interconnects for VLSI", pp. 84-175						
TT	AM	Silicon Processing for the VLSI ERA - "Refractory Metals and Their Silicides in VLSI Fabrication", pp. 384-406						
	AN							
	AO							
	AP							
	AQ							
	AR							

EXAMINER

Thien Lam

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09-02-99

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.